

MOSFET
OptiMOS™ 6 Power-Transistor, 150 V

Features

- N-channel, normal level
- Very low on-resistance $R_{DS(on)}$
- Superior thermal resistance
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- MSL 1 classified according to J-STD-020

Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	150	V
$R_{DS(on),max}$	5.5	mΩ
I_D	130	A
Q_{oss}	130	nC
Q_G	43	nC
Q_{rr} (500 A/μs)	105	nC

Type/Ordering Code	Package	Marking	Related Links
ISC055N15NM6	PG-TDSON-8	055N15N6	-

PG-TDSON-8 FL

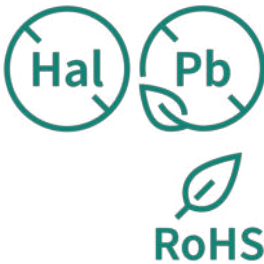
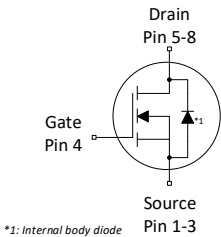
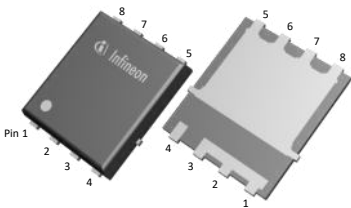




Table of Contents

Description 1

Maximum ratings 3

Thermal characteristics 3

Electrical characteristics 4

Electrical characteristics diagrams 6

Package Outlines 10

Revision History 13

Trademarks 13

Disclaimer 13

1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	130 92 85 15.4	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=8\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=50\text{ °C/W}$ ²⁾
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	520	A	$T_C=25\text{ °C}$
Avalanche current, single pulse ⁴⁾	I_{AS}	-	-	50	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse	E_{AS}	-	-	749	mJ	$I_D=13\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	214 3.0	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=50\text{ °C/W}$ ²⁾
Operating and storage temperature	T_j , T_{stg}	-55	-	175	°C	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information

⁴⁾ See Diagram 13 for more detailed information

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	-	0.7	°C/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	-	20	°C/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ⁵⁾	R_{thJA}	-	-	50	°C/W	-

⁵⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	150	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	3.0	3.5	4.0	V	$V_{DS}=V_{GS}$, $I_D=110\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	4.5 5.0 5.6	5.2 5.5 6.4	m Ω	$V_{GS}=15\text{ V}$, $I_D=50\text{ A}$ $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$ $V_{GS}=8\text{ V}$, $I_D=25\text{ A}$
Gate resistance	R_G	-	0.74	1.11	Ω	-
Transconductance	g_{fs}	42	85	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}$, $I_D=50\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Input capacitance ⁶⁾	C_{iss}	-	3100	4000	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Output capacitance ⁶⁾	C_{oss}	-	970	1300	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance ⁶⁾	C_{rss}	-	14	21	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	12	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=25\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	6	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=25\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	16	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=25\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	8	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=25\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

⁶⁾ Defined by design. Not subject to production test.

Table 6 Gate charge characteristics ⁷⁾

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Gate to source charge ⁸⁾	Q_{gs}	-	16.6	22	nC	$V_{DD}=75\text{ V}$, $I_D=25\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	10.8	-	nC	$V_{DD}=75\text{ V}$, $I_D=25\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge ⁸⁾	Q_{gd}	-	10.1	15.2	nC	$V_{DD}=75\text{ V}$, $I_D=25\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	15.9	-	nC	$V_{DD}=75\text{ V}$, $I_D=25\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ⁸⁾	Q_g	-	43	56	nC	$V_{DD}=75\text{ V}$, $I_D=25\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	$V_{DD}=75\text{ V}$, $I_D=25\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	36	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ⁸⁾	Q_{oss}	-	130	169	nC	$V_{DS}=75\text{ V}$, $V_{GS}=0\text{ V}$

⁷⁾ See "Gate charge waveforms" for parameter definition

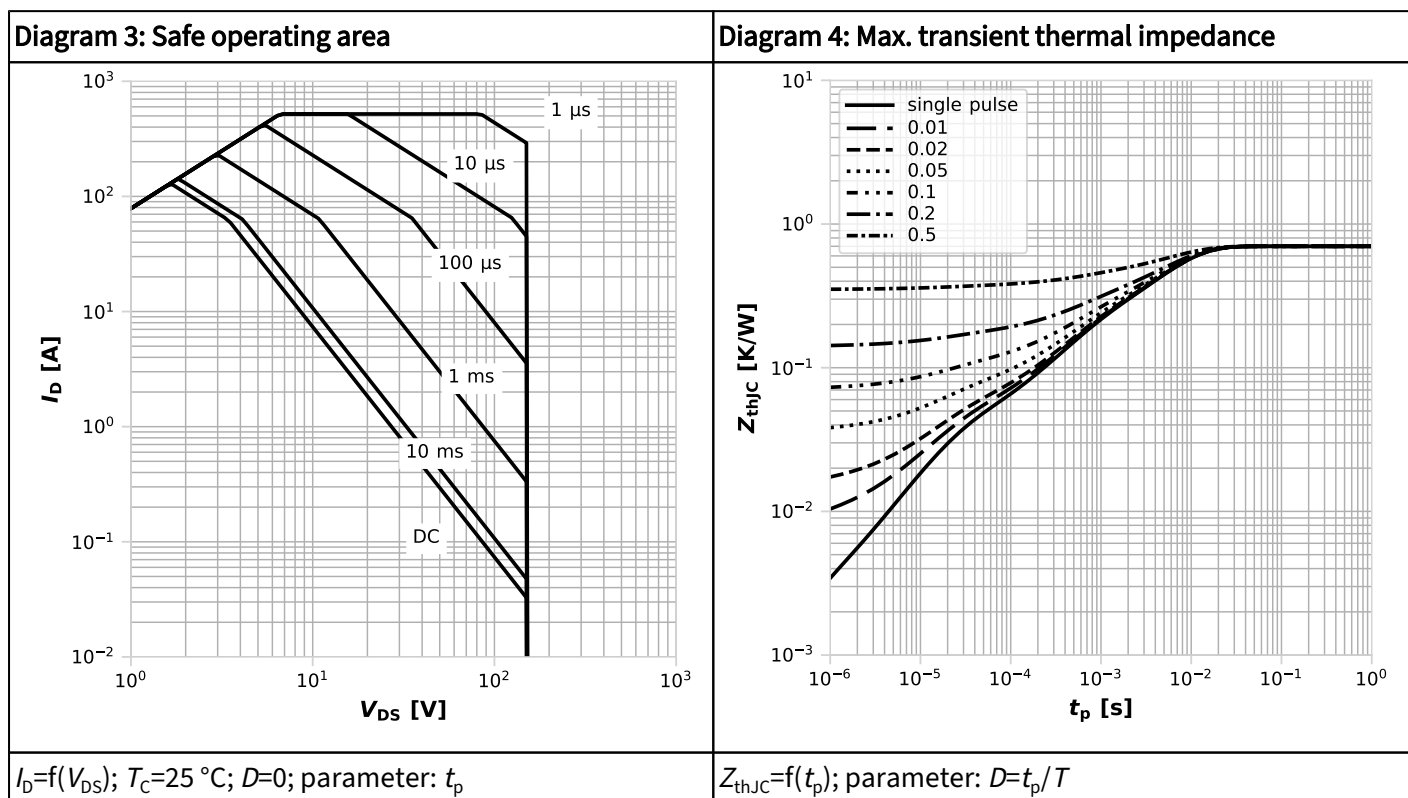
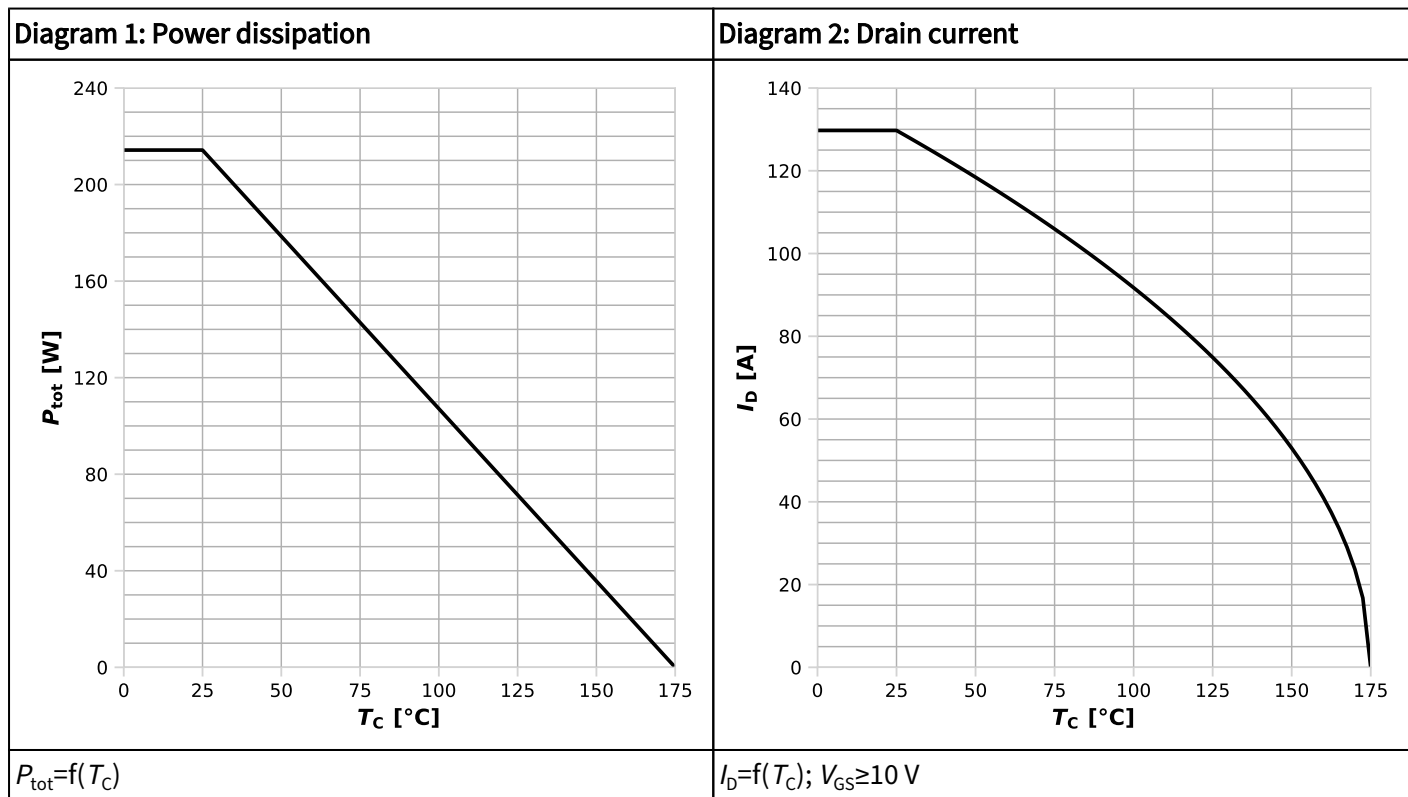
⁸⁾ Defined by design. Not subject to production test.

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	130	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	520	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.85	1.0	V	$V_{GS}=0\text{ V}$, $I_F=50\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery time ⁹⁾	t_{rr}	-	30	60	ns	$V_R=75\text{ V}$, $I_F=25\text{ A}$, $di_F/dt=500\text{ A}/\mu\text{s}$
Reverse recovery charge ⁹⁾	Q_{rr}	-	105	210	nC	$V_R=75\text{ V}$, $I_F=25\text{ A}$, $di_F/dt=500\text{ A}/\mu\text{s}$
Reverse recovery time ⁹⁾	t_{rr}	-	26	52	ns	$V_R=75\text{ V}$, $I_F=25\text{ A}$, $di_F/dt=1000\text{ A}/\mu\text{s}$
Reverse recovery charge ⁹⁾	Q_{rr}	-	195	390	nC	$V_R=75\text{ V}$, $I_F=25\text{ A}$, $di_F/dt=1000\text{ A}/\mu\text{s}$

⁹⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams



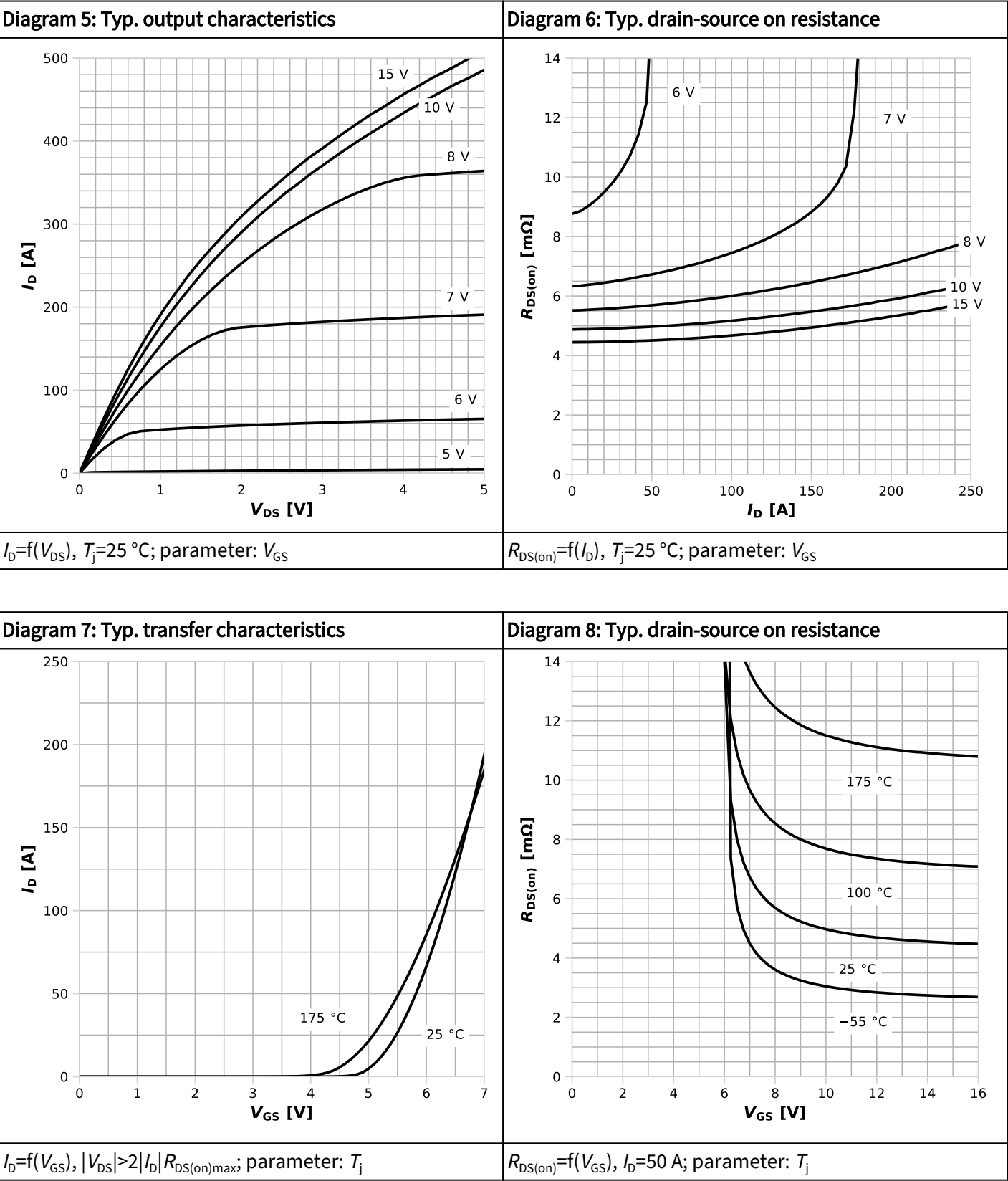
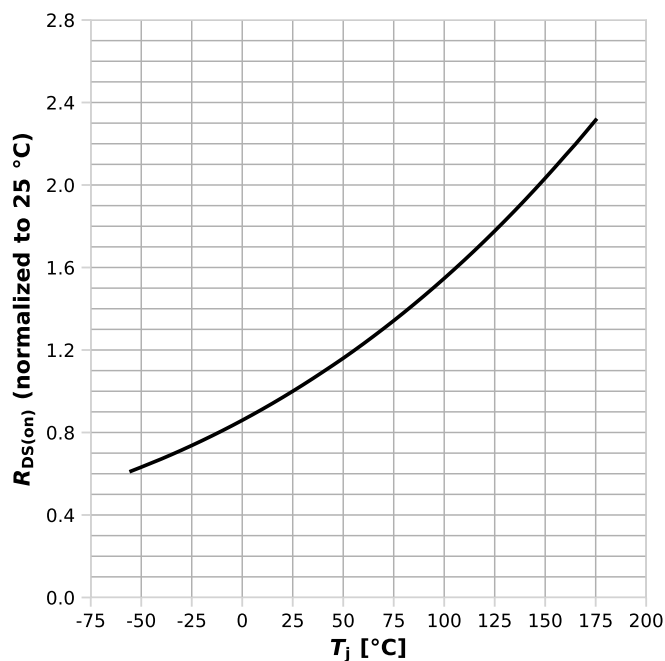
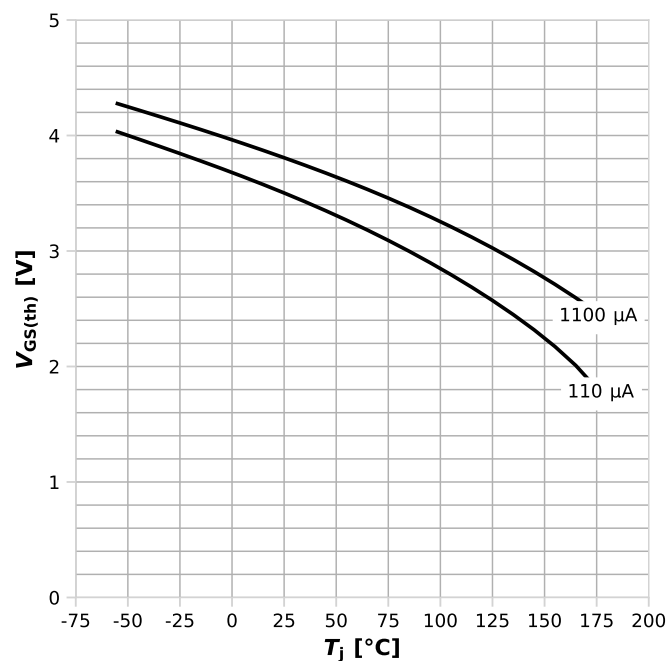


Diagram 9: Normalized drain-source on resistance



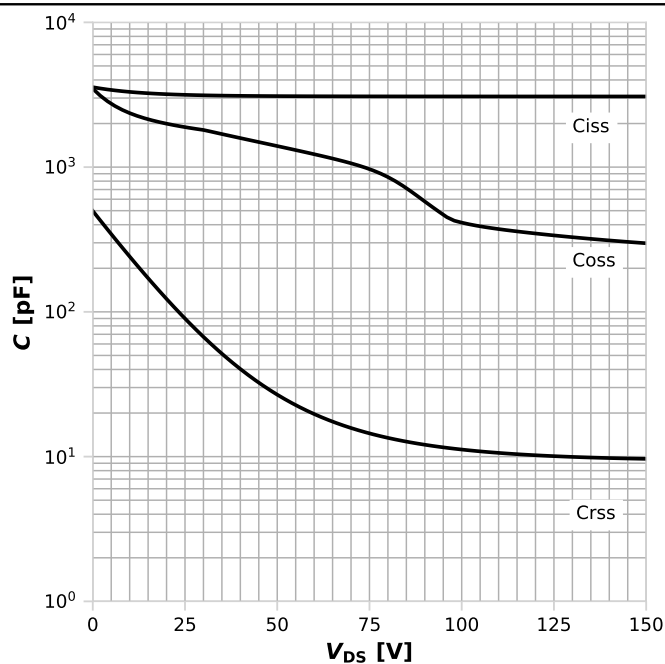
$$R_{DS(on)} = f(T_j), I_D = 50 \text{ A}, V_{GS} = 10 \text{ V}$$

Diagram 10: Typ. gate threshold voltage



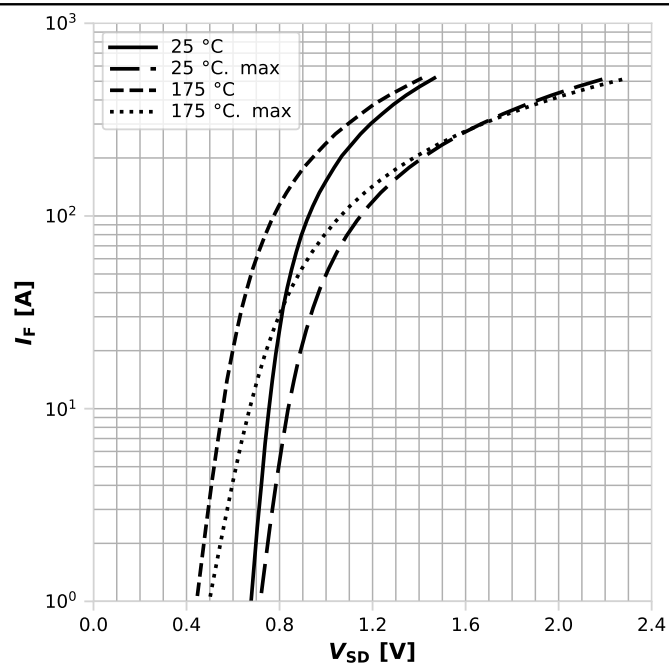
$$V_{GS(th)} = f(T_j), V_{GS} = V_{DS}; \text{ parameter: } I_D$$

Diagram 11: Typ. capacitances

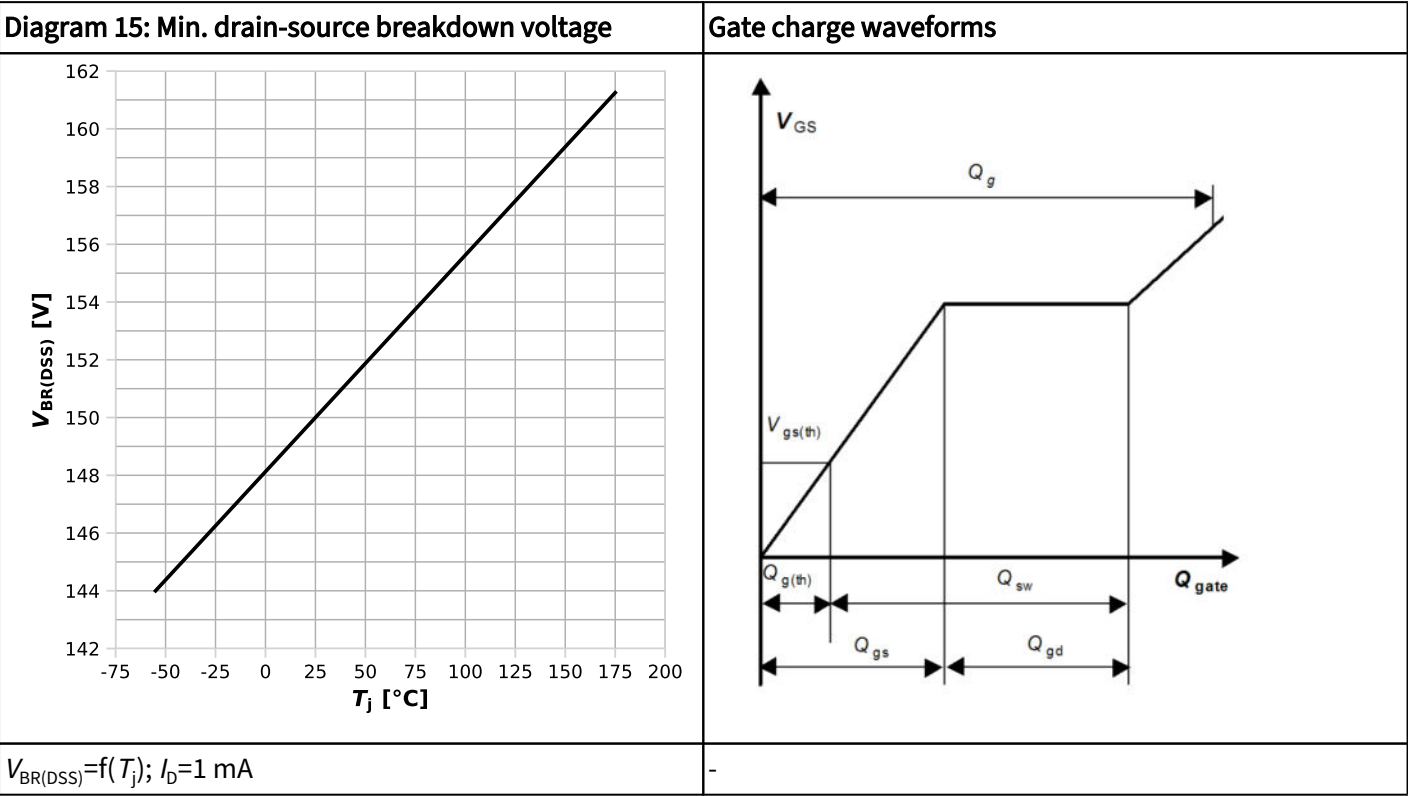
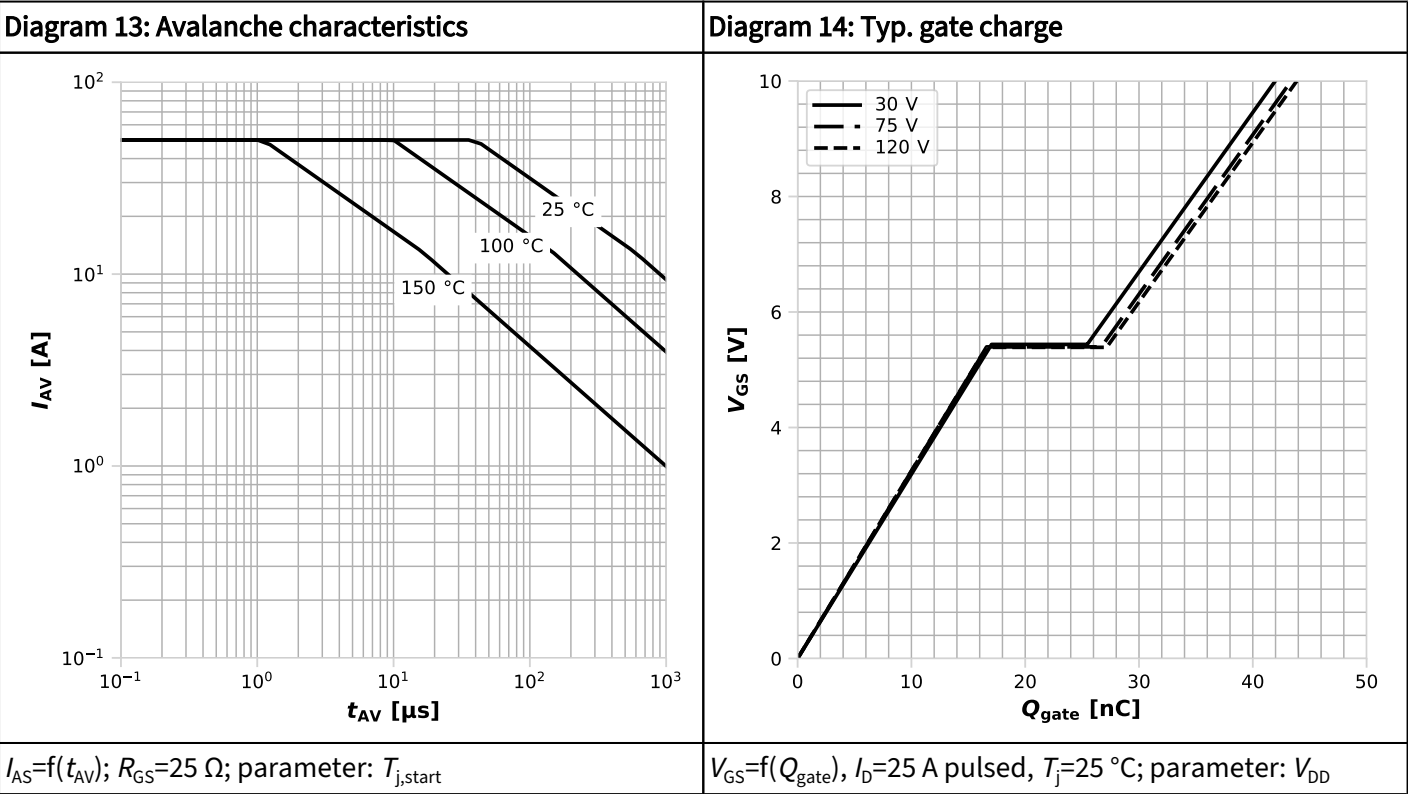


$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 12: Forward characteristics of reverse diode



$$I_F = f(V_{SD}); \text{ parameter: } T_j$$



5 Package Outlines

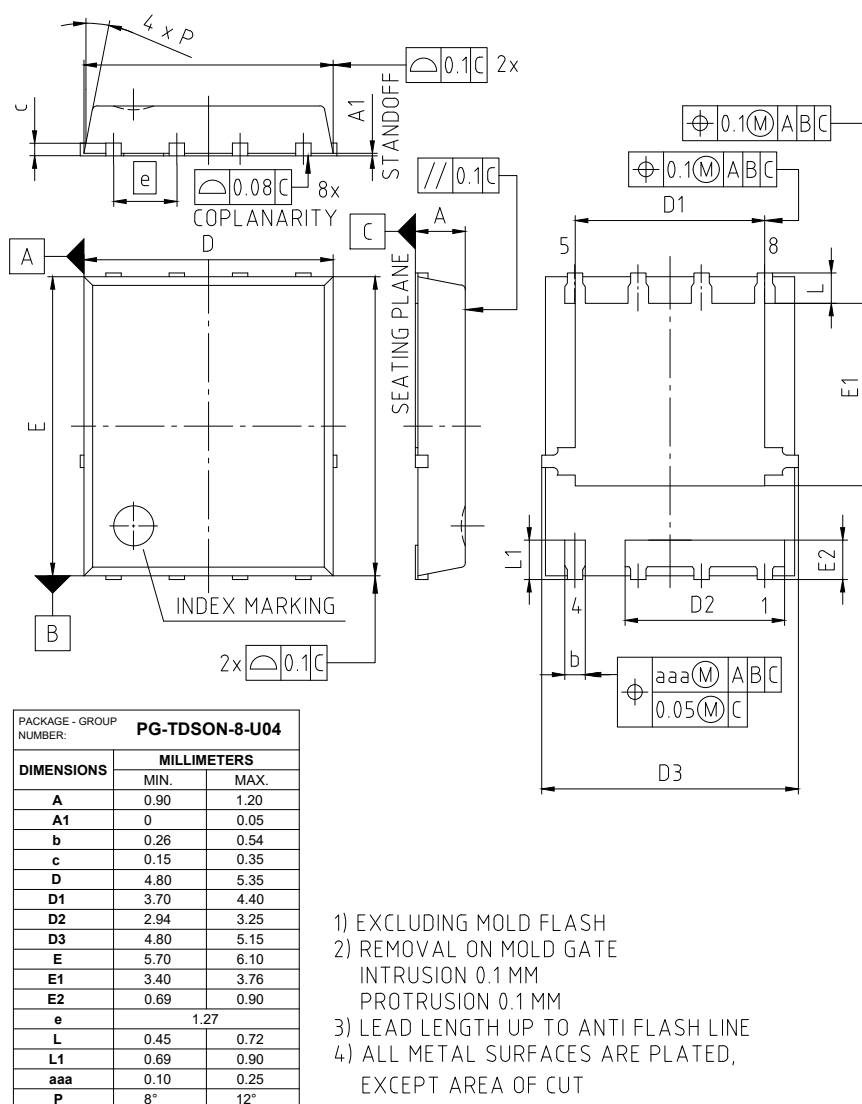


Figure 1 Outline PG-TDSON-8, dimensions in mm

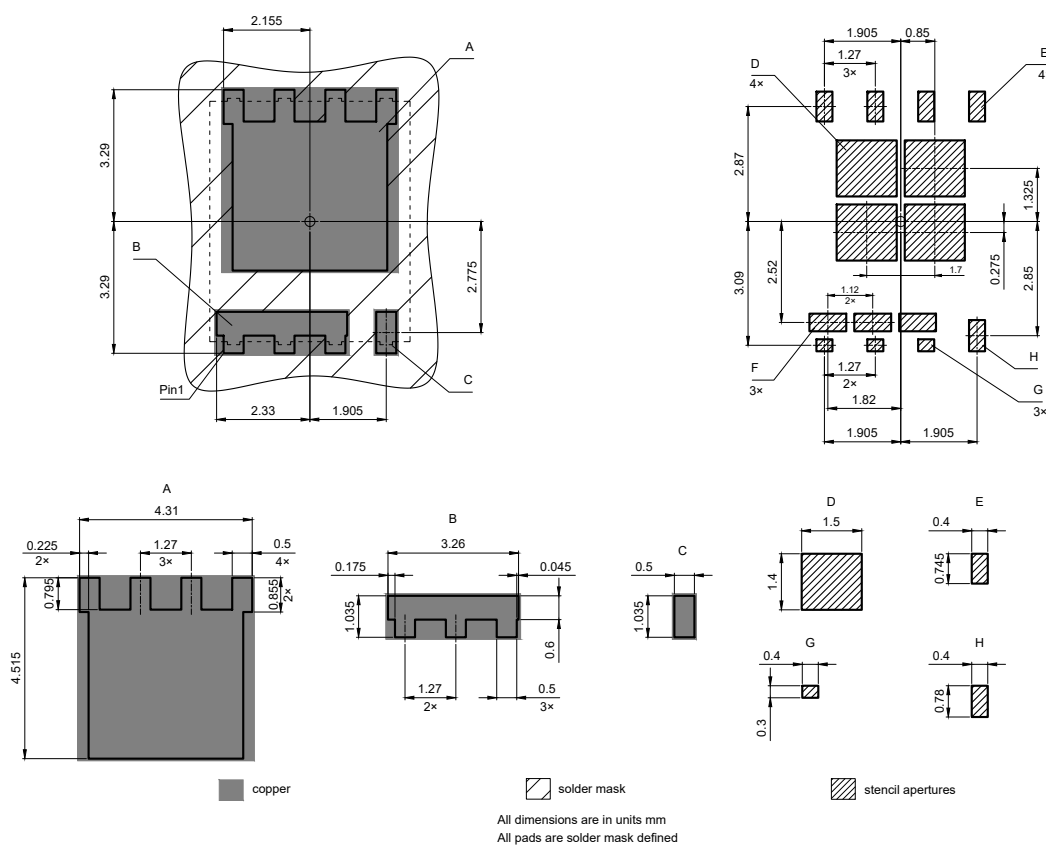


Figure 2 Outline PG-TDSON-8, dimensions in mm

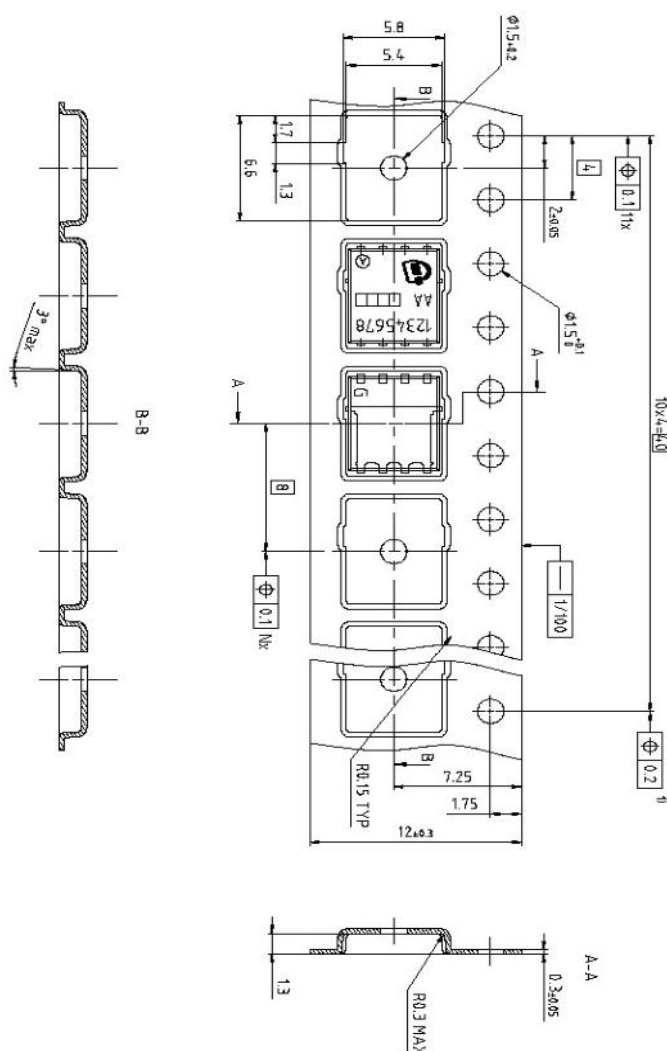


Figure 3 Outline PG-TDSON-8, dimensions in mm

Revision History

ISC055N15NM6

Revision 2024-04-19, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
1.0	2024-03-15	Release of preliminary version
2.0	2024-04-19	Release of final

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